PATENT COOPERATION TREATY

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INTERNATIONAL PRELIMINARY REPORTON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

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	's or agent's file refe LPCTMES	erence	FOR FURTHER ACT	ION .	See Form PCT/IPEA/416	
International application No. International filing date (d		lay/month/year)	Priority date (day/month/year)			
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Int.Cl 7	H01L21/02,	H01L2	21/205,C03B29,	/36, C03B29	/06	
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1. T	his report is the intaction uthority under Artic	ernational p cle 35 and tr	reliminary examination ransmitted to the applicant	eport, established by according to Article	y this International Prelimin 36.	ary Examining
2. T	his REPORT consis	ts of a total	of 3sheets, in	ncluding this cover sl	heet.	
		•	y ANNEXES, comprising	_	•	· ·
· a.	a total of_	<u> </u>	sheets, as follows:	•		
	she	ets of the de	scription, claims and/or di	awings which have b	een amended and are the bas	sis of this report
•	and	Vor sheets co	ontaining rectifications au Instructions).	thorized by this Auth	ority (see Rule 70.16 and See	ction 607 of the
	she	ets which so	persede earlier sheets bu	t which this Authorit	y considers contain an amend	dment that coes
	bey	ond the disc	losure in the international	application as filed,	as indicated in item 4 of Box	No. I and the
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	containing	a sequence	listing and/or tables rela-	ted thereto, in comp	uter readable form only, as i the Administrative Instructio	indicated in the
4. T	his report contains i	ndications re	elating to the following ite	ems:		
9	Box No. I	Basis of the	e report			
	Box No. II	Priority				,
. [Box No. III	Non-establ	ishment of opinion with re	egard to novelty, inv	entive step and industrial app	olicability
. [Box No. IV	Lack of uni	ty of invention	•		,
	Box No. V	Reasoned s citations an	tatement under Article 35(d explanations supporting	2) with regard to nove s such statement	elty, inventive step or industri	al applicability;
	Box No. VI	Certain doc	uments cited		·	
	Box No. VII	Certain def	ects in the international ap	plication		
	Box No. VIII	Certain obs	ervations on the internation	onal application		
Date of s	ubmission of the der	mand	_	Date of completion	n of this report	
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Name and	Name and mailing address of the IPEA/JP Authorized officer					4L 9170
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BOX NO.). I	Basis of the report
1. Wit	th regard	d to the language this report is board on the internal to the
oth	erwise in	d to the language, this report is based on the international application in the language in which it was filed, unless
	This	report is based on translations from the original language interest of the
	whic	ch is the language of a translation furnished for the purposes of:
		international search (under Rules 12.3 and 23.1(b))
		publication of the international application (under Rule 12.4)
		international preliminary examination (under Rules 55.2 and/or 55.3)
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2. With	h regard	d to the elements of the international application, this report is based on (replacement sheets which have been
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and c	are not a	annexed to this report):
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ت		nternational application as originally filed/furnished
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3.	The ar	mendments have resulted in the cancellation of:
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		the drawings, sheets/figs
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	made, s	since they have been considered to go beyond the disclosure as filed, as indicated in the Supplemental Box 70.2(c)).
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Box No. V R	easoned statement u tations and explana	nder Article : tions support	35(2) with regard to novelty, inventing such statement	tive step or industrial applicability;
1. Statement				
Novelty	(11)	Claims Claims	1-5	YES NO
Inventive	step (IS)	Claims Claims	1-5	YES
·Industrial ·	applicability (IA)	Claims Claims	1-5	YES
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2. Citations and explanations (Rule 70.7)

The following documents have been considered for the purpose of this report:

D1. EP 916750 A1(NIPPON PILLAR PACKING CO., LTD.)1999.05,19 D2. JP 10-55975 A(HITACHI, CO., LTD.)1998.02.24

The subject matter of claim 1-5 does not appear to involve an inventive step in view of the document 1 cited in the ISR and the document 2 cited in the same.

D1 discloses the purpose to provide the large-diameter SiC wafer. D2 discloses the technical feature of a small-diameter single crystal wafer placed in the center of the wafer, and large-diameter polycrystal wafer manufactured by a CVD method to provide the large-size wafer. The technical feature in D1 and D2 are concerned with mutually related technical field, which is wafer manufacturing. Although D1 does not disclose the technical feature of SiC wafer, both the D1 and D2 have the same purpose, that is providing the large-size wafer.

Therefore, the purpose disclosed in D1 and the technical feature disclosed in D2 could constitute the present invention, which would have been easily conceived by the person skilled in the art.